



**DGD2104M** 

#### HALF-BRIDGE GATE DRIVER IN SO-8

#### Description

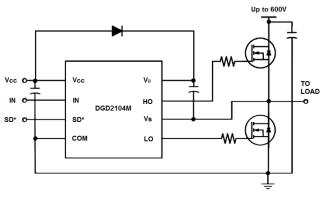
The DGD2104M is a high-voltage / high-speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. High-voltage processing techniques enable the DGD2104M's high side to switch to 600V in a bootstrap operation.

The DGD2104M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high-pulse current buffers designed for minimum driver cross conduction.

The DGD2104M is offered in the SO-8 package and operates over an extended -40°C to +125°C temperature range.

### Applications

- DC-DC Converters
- DC-AC Inverters
- AC-DC Power Supplies
- Motor Controls
- Class D Power Amplifiers



Typical Configuration

# Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in a Half Bridge Configuration
- 290mA Source / 600mA Sink Output Current Capability
- Designed for Enhanced Performance in Noisy Motor Applications
- Outputs Tolerant to Negative Transients
- Internal Dead Time to Protect MOSFETs
- Wide Low-Side Gate Driver Supply Voltage: 10V to 20V
- Logic Input (IN and SD\*) 3.3V Capability
- Schmitt Triggered Logic Inputs
- Undervoltage Lockout for V<sub>CC</sub> (Logic and Low Side Supply)
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

- Case: SO-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads
  Solderable per MIL-STD-202, Method 208 (9)
- Weight: 0.074 grams (Approximate)



### Ordering Information (Note 4)

F	Part Number	Marking	Reel Size (inch)	Tape Width (mm)	Quantity per Reel
DG	D2104MS8-13	DGD2104M	13	12	2,500
Notes:	1. No purposely adde	ed lead. Fully EU Directive 2002/9	5/EC (RoHS), 2011/65/EU (RoHS	2) & 2015/863/EU (RoHS 3) com	pliant.

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

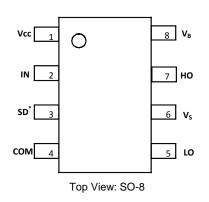
### **Marking Information**



)¦¦ = Manufacturer's Marking DGD2104M = Product Type Marking Code YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



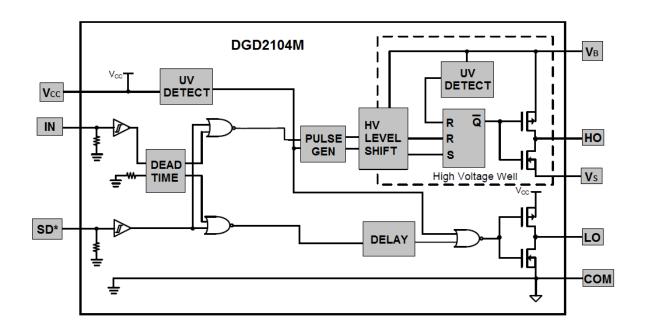
# Pin Diagrams



## **Pin Descriptions**

Pin Number	Pin Name	Function
1	V <sub>CC</sub>	Logic and Low Side Supply
2	IN	Logic Input for High-Side and Low-Side Gate Driver Outputs (HO and LO), in Phase with HO
3	SD*	Logic input for Shutdown, Enabled Low
4	COM	Low-Side and Logic Return
5	LO	Low-Side Gate Drive Output
6	Vs	High-Side Floating Supply Return
7	HO	High-Side Gate Drive Output
8	VB	High-Side Floating Supply

# **Functional Block Diagram**





#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	VB	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	Vs	V <sub>B</sub> -24 to V <sub>B</sub> +0.3	V
High-Side Floating Output Voltage	V <sub>HO</sub>	V <sub>S</sub> -0.3 to V <sub>B</sub> +0.3	V
Offset Supply Voltage Transient	dVs / dt	50	V/ns
Low-Side Fixed Supply Voltage	V <sub>CC</sub>	-0.3 to +24	V
Low-Side Output Voltage	V <sub>LO</sub>	-0.3 to V <sub>CC</sub> +0.3	V
Logic Input Voltage (IN and SD*)	V <sub>IN</sub>	-0.3 to V <sub>CC</sub> +0.3	V

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	PD	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	200	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

### **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High Side Floating Supply Absolute Voltage	VB	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
High Side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High Side Floating Output Voltage	V <sub>HO</sub>	Vs	VB	V
Low Side Fixed Supply Voltage	Vcc	10	20	V
Low Side Output Voltage	V <sub>LO</sub>	0	V <sub>CC</sub>	V
Logic Input Voltage (IN and SD*)	V <sub>IN</sub>	0	5	V
Ambient Temperature	T <sub>A</sub>	-40	+125	°C

Note: 6. Logic operation for Vs of -5V to +600V.



#### **DC Electrical Characteristics** (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, @T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Logic "1" (IN) & Logic "0" (SD*) Input Voltage (Note 8)	VIH	2.5	_	-	V	$V_{CC} = 10V$ to 20V
Logic "0" (IN) & Logic "1" (SD*) Input Voltage (Note 8)	VIL	_	-	0.8	V	$V_{CC} = 10V$ to 20V
High Level Output Voltage, V <sub>BIAS</sub> - V <sub>O</sub>	V <sub>OH</sub>	_	0.05	0.2	V	$I_0 = 2mA$
Low Level Output Voltage, Vo	Vol	_	0.02	0.1	V	$I_0 = 2mA$
Offset Supply Leakage Current	I <sub>LK</sub>	—	-	50	μA	$V_B = V_S = 600V$
Quiescent V <sub>BS</sub> Supply Current	I <sub>BSQ</sub>	—	60	100	μA	$V_{IN} = 0V \text{ or } 5V$
Quiescent V <sub>CC</sub> Supply Current	ICCQ1	-	350	500	μA	$V_{IN} = 0V \text{ or } 5V, SD^* = 5V$
Quiescent V <sub>CC</sub> Supply Current in Shutdown	I <sub>CCQ2</sub>	—	590	750	μA	$V_{IN} = 0V \text{ or } 5V, SD^* = 0V$
Logic "1" Input Bias Current	I <sub>IN+</sub>	—	3.0	10	μA	$V_{IN} = 5V, SD^* = 0V$
Logic "0" Input Bias Current	I <sub>IN-</sub>	—	-	5.0	μA	$V_{IN} = 0V, SD^* = 5V$
V <sub>CC</sub> Supply Undervoltage Positive Going Threshold	V <sub>CCUV+</sub>	8.0	8.9	9.8	V	—
V <sub>CC</sub> Supply Undervoltage Negative Going Threshold	Vccuv-	7.4	8.2	9.0	V	—
V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	V <sub>BSUV+</sub>	4.5	5.5	6.5	V	—
V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	V <sub>BSUV-</sub>	4.2	5.2	6.2	V	-
Output High Short Circuit Pulsed Current	I <sub>O+</sub>	130	290	_	mA	V <sub>O</sub> = 0V, PW ≤ 10µs
Output Low Short Circuit Pulsed Current	I <sub>O-</sub>	270	600	_	mA	V <sub>O</sub> = 15V, PW ≤ 10µs

Notes: 7. The V<sub>IN</sub> and I<sub>IN</sub> parameters are applicable to the two logic pins: IN and SD\*. The V<sub>O</sub> and I<sub>O</sub> parameters are applicable to the respective output pins: HO and LO.

8. For optimal operation, it is recommended that the input pulses (IN and SD\*) should have an minimum amplitude of 2.5V with a minimum pulse width of 840ns.

# AC Electrical Characteristics (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, C<sub>L</sub> = 1000pF, @T<sub>A</sub> = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Turn-On Propagation Delay	t <sub>ON</sub>	-	680	820	ns	$V_{\rm S} = 0V$
Turn-Off Propagation Delay	tOFF	-	150	220	ns	$V_{\rm S} = 600 V$
Shutdown Propagation Delay	t <sub>SD</sub>	-	160	220	ns	-
Delay Matching, HO and LO Turn-On / Turn-Off	t <sub>DM</sub>	-	Ι	60	ns	—
Turn-On Rise Time	t <sub>R</sub>	-	70	170	ns	$V_{\rm S} = 0V$
Turn-Off Fall Time	t <sub>F</sub>	-	35	90	ns	$V_{\rm S} = 0V$
Deadtime: t <sub>DT LO-HO</sub> & t <sub>DT HO-LO</sub>	t <sub>DT</sub>	300	420	650	ns	_



# **Timing Waveforms**

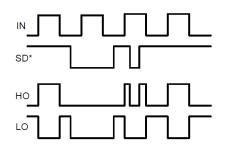


Figure 1. Input / Output Timing Diagram

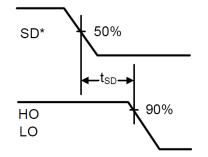
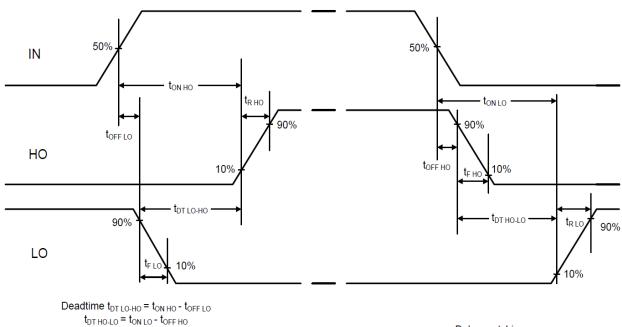
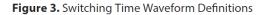


Figure 2. Shutdown Waveform Definition



Deadtime matching t<sub>MDT</sub> = t<sub>DT LO-HO</sub> - t<sub>DT HO-LO</sub>  $\begin{array}{l} \text{Delay matching} \\ t_{\text{DM OFF}} = t_{\text{OFF LO}} - t_{\text{OFF HO}} \\ t_{\text{DM ON}} = t_{\text{ON LO}} - t_{\text{ON HO}} \end{array}$ 





# Typical Performance Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

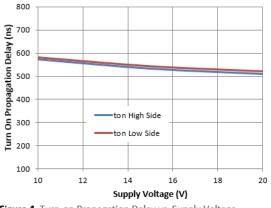


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

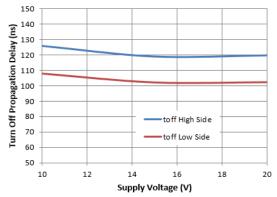
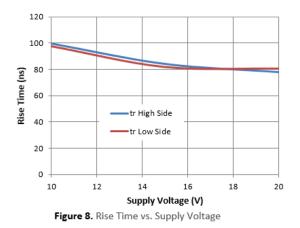


Figure 6. Turn-off Propagation Delay vs. Supply Voltage



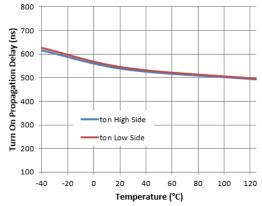


Figure 5. Turn-on Propagation Delay vs. Temperature

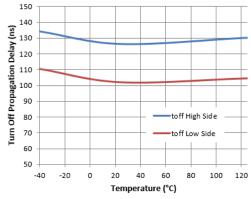
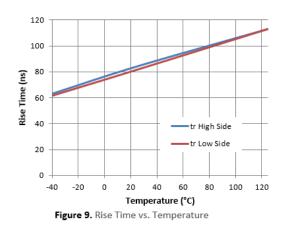
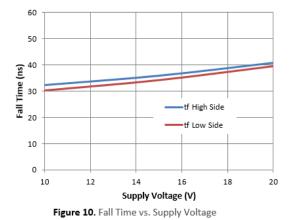


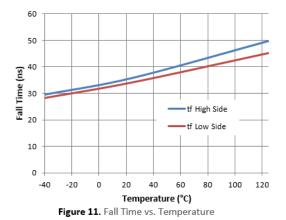
Figure 7. Turn-off Propagation Delay vs. Temperature





# Typical Performance Characteristics (continued)





800 700 •ICC q IBSa 600 Quiescent Current (µA) 500 400 300 200 100 0 12 14 16 18 20 10 Supply Voltage (V)

Figure 12. Quiescent Current vs. Supply Voltage

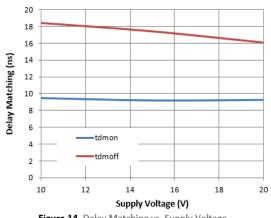
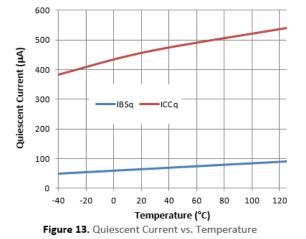


Figure 14. Delay Matching vs. Supply Voltage



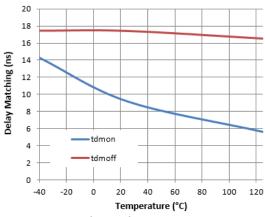
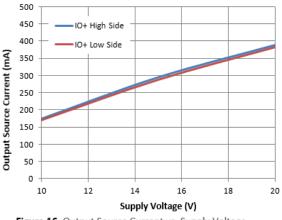


Figure 15. Delay Matching vs. Temperature



# Typical Performance Characteristics (continued)



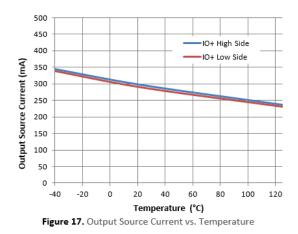
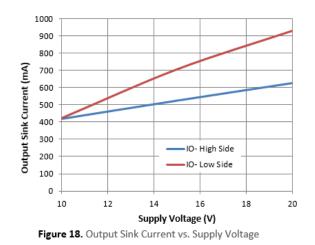


Figure 16. Output Source Current vs. Supply Voltage



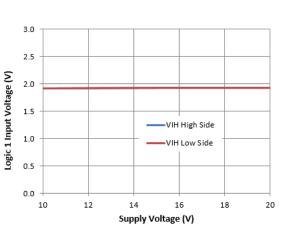
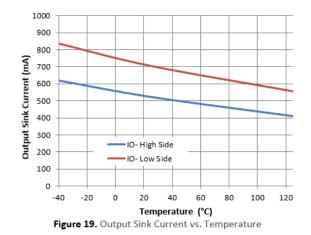


Figure 20. Logic 1 Input Voltage vs. Supply Voltage



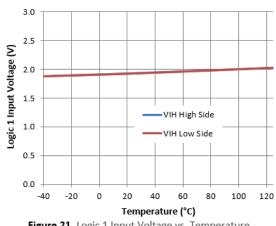
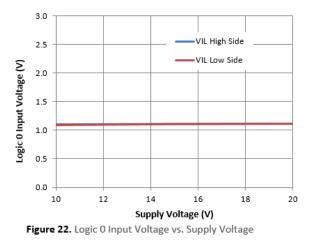


Figure 21. Logic 1 Input Voltage vs. Temperature



# Typical Performance Characteristics (continued)



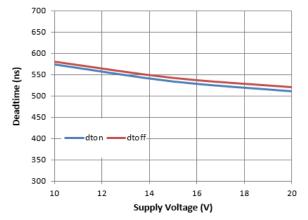
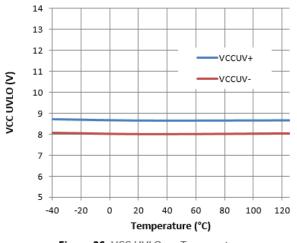


Figure 24. Deadtime vs. Supply Voltage





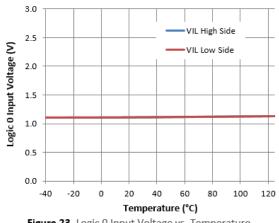


Figure 23. Logic 0 Input Voltage vs. Temperature

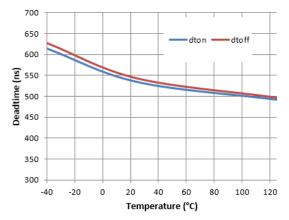


Figure 25. Deadtime vs. Temperature

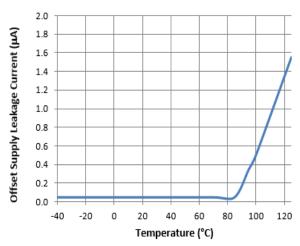


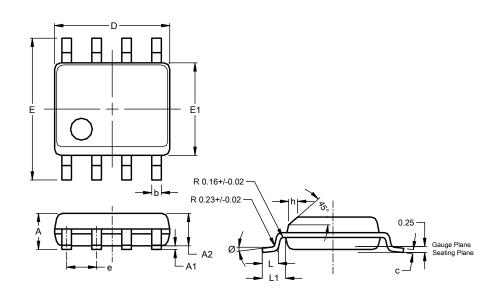
Figure 27. Offset Supply Leakage Current vs. Temperature



DGD2104M

#### **Package Outline Dimensions**

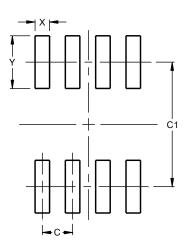
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8 (Type TH)							
Dim	Min	Max	Тур				
Α	1.35	1.75					
A1	0.10	0.25					
A2	-		1.45				
b	0.35	0.51					
С	0.190	0.248	-				
D	4.80	5.00	4.90				
E	5.80	6.20	6.00				
E1	3.80	4.00	3.90				
е			1.27				
h	0.25	0.50					
L	0.41	1.27					
L1			1.04				
Ø	0°	8°	-				
All Dimensions in mm							

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
C1	5.20
Х	0.60
Y	2.20

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

#### SO-8 (Type TH)

SO-8 (Type TH)



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com